JST12A-800SW 12A TRIAC

(I)-33.6 (AC))]TJ 0.584 398I

Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D = V_{DRM} T_j =125 R_L =3.3k	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	25	mA
				30	
I_H	I_T =500mA		MAX.	15	mA
dV/dt	V_D=540V Gate Open T_j =125		MIN.	400	V s
(dI/dt)c	(dV/dt)c=1 9 V_j=125		MIN.	3	A/ms
t_{on}	I_G=20mA I_A=200mA I_R=20mA T_j=25		TYP.	2.5	s
t_{off}				25	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX .)	Unit
V_{TM}	I_{TM} =17A t_p=380 s	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=125	0.77	V
R_D	Dynamic resistance	T_j=125	35	P
I_{DRM}	V_D = V_{DRM} V_R = V_{RRM}	T_j=25	5	A
I_{RRM}		T_j=125	0.5	mA

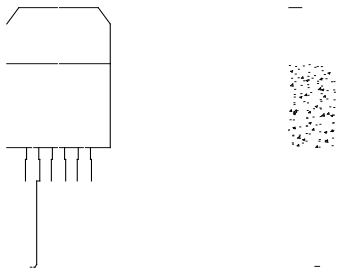
THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.3	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



PACKAGE MECHANICAL DATA



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